

## SMALL SIGNAL NPN TRANSISTORS

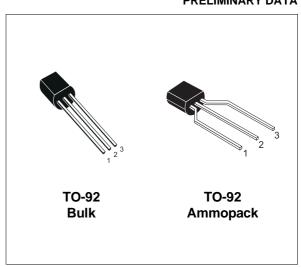
#### **PRELIMINARY DATA**

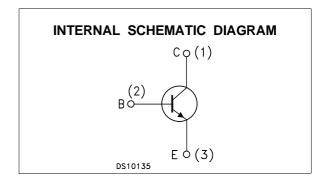
Ordering Code	Marking	Package / Shipment
BC337-25	BC337-25	TO-92 / Bulk
BC337-25-AP	BC337-25	TO-92 / Ammopack
BC337-40	BC337-40	TO-92 / Bulk
BC337-40-AP	BC337-40	TO-92 / Ammopack

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- THE PNP COMPLEMENTARY TYPES ARE BC327-25 AND BC327-40 RESPECTIVELY

#### **APPLICATIONS**

- WELL SUITABLE FOR TV AND HOME APPLIANCE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE





### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage (I <sub>E</sub> = 0)	50	V
VCEO	Collector-Emitter Voltage (I <sub>B</sub> = 0)	45	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)	5	V
Ic	Collector Current	0.5	Α
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5 ms)	1	Α
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25 °C	625	mW
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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### THERMAL DATA

R <sub>thj-amb</sub> •	Thermal Resistance	Junction-Ambient	Max	200	°C/W	
R <sub>thj-case</sub> •	Thermal Resistance	Junction-Case	Max	83.3	°C/W	

# **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

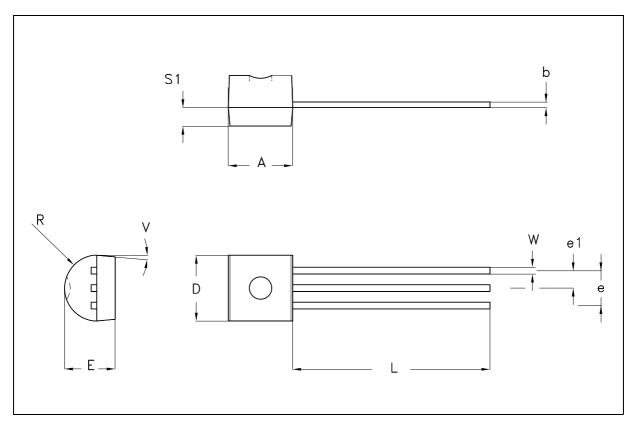
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 20 V V <sub>CB</sub> = 20 V T <sub>C</sub> = 150 °C			100 5	nΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			100	nA
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 10 μA	50			V
V <sub>(BR)CEO*</sub>	Collector-Emitter Breakdown Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA	45			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10 μA	5			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	$I_{C} = 500 \text{ mA}$ $I_{B} = 50 \text{ mA}$			0.7	V
V <sub>BE(on)</sub> *	Base-Emitter On Voltage	I <sub>C</sub> = 500 mA			1.2	V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 100 mA	160 250		400 600	
f⊤	Transition Frequency	$I_{C} = 10 \text{ mA } V_{CE} = 5 \text{ V } f = 100 \text{MHz}$	100			MHz
Ссво	Collector-Base Capacitance	I <sub>E</sub> = 0 V <sub>CB</sub> = 10 V f = 1 MHz		5		pF

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

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### **TO-92 MECHANICAL DATA**

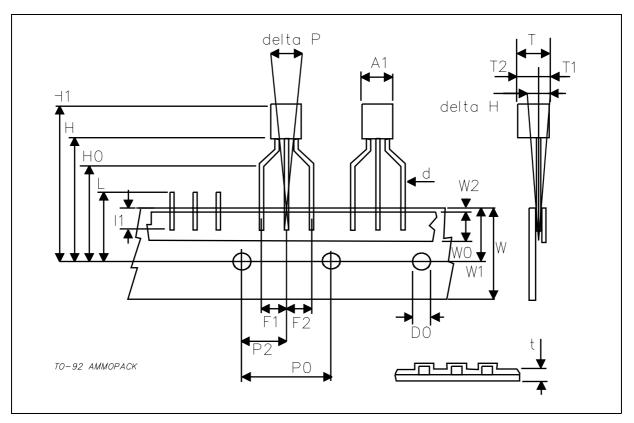
DIM.	mm			inch		
Dim	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
Е	3.30		3.94	0.130		0.155
е	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.609
R	2.16		2.41	0.085		0.094
S1	1.14		1.52	0.045		0.059
W	0.41		0.56	0.016		0.022
V	4 degree		6 degree	4 degree		6 degree



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## TO-92 AMMOPACK SHIPMENT (Suffix"-AP") MECHANICAL DATA

DIM.	mm			inch			
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
A1			4.80			0.189	
T			3.80			0.150	
T1			1.60			0.063	
T2			2.30			0.091	
d			0.48			0.019	
P0	12.50	12.70	12.90	0.492	0.500	0.508	
P2	5.65	6.35	7.05	0.222	0.250	0.278	
F1,F2	2.44	2.54	2.94	0.096	0.100	0.116	
delta H	-2.00		2.00	-0.079		0.079	
W	17.50	18.00	19.00	0.689	0.709	0.748	
W0	5.70	6.00	6.30	0.224	0.236	0.248	
W1	8.50	9.00	9.25	0.335	0.354	0.364	
W2			0.50			0.020	
Н	18.50		20.50	0.728		0.807	
H0	15.50	16.00	16.50	0.610	0.630	0.650	
H1			25.00			0.984	
D0	3.80	4.00	4.20	0.150	0.157	0.165	
t			0.90			0.035	
L			11.00			0.433	
l1	3.00			0.118			
delta P	-1.00		1.00	-0.039		0.039	



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